

PMEGxx05ET series

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

Rev. 02 — 13 January 2010

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT23 small Surface Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
PMEG2005ET	SOT23	-	single diode
PMEG3005ET	SOT23	-	single diode
PMEG4005ET	SOT23	-	single diode

1.2 Features

- Forward current: 0.5 A
- Very low forward voltage
- Small SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

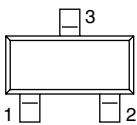
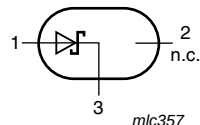
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_F	forward current		-	-	0.5	A
V_R	reverse voltage					
	PMEG2005ET		-	-	20	V
	PMEG3005ET		-	-	30	V
	PMEG4005ET		-	-	40	V
V_F	forward voltage	$I_F = 500 \text{ mA}$ [1]				
	PMEG2005ET		-	355	390	mV
	PMEG3005ET		-	380	430	mV
	PMEG4005ET		-	420	470	mV

[1] Pulse test: $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$.

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	anode		
2	not connected		
3	cathode		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2005ET	-	plastic surface mounted package; 3 leads	SOT23
PMEG3005ET	-	plastic surface mounted package; 3 leads	SOT23
PMEG4005ET	-	plastic surface mounted package; 3 leads	SOT23

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG2005ET	P3*
PMEG3005ET	P4*
PMEG4005ET	P5*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage				
	PMEG2005ET		-	20	V
	PMEG3005ET		-	30	V
	PMEG4005ET		-	40	V
I_F	forward current		-	0.5	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ ms; $\delta \leq 0.5$	-	3.9	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8$ ms square wave	^[1] -	10	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	^[1] -	280	mW
			^[2] -	420	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	^{[1][2]} -	-	440	K/W
			^{[1][3]} -	-	300	K/W

- [1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

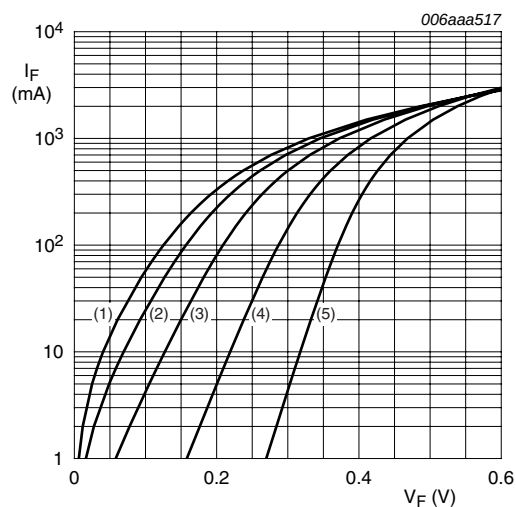
7. Characteristics

Table 8. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

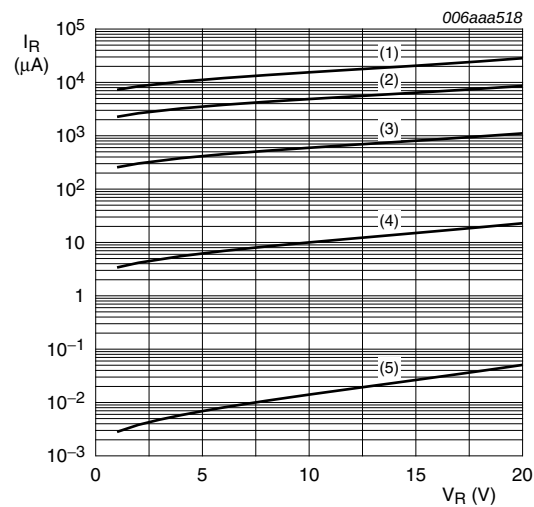
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage		[1]			
	PMEG2005ET	$I_F = 0.1\text{ mA}$	-	90	130	mV
		$I_F = 1\text{ mA}$	-	150	190	mV
		$I_F = 10\text{ mA}$	-	210	240	mV
		$I_F = 100\text{ mA}$	-	280	330	mV
		$I_F = 500\text{ mA}$	-	355	390	mV
	PMEG3005ET	$I_F = 0.1\text{ mA}$	-	90	130	mV
		$I_F = 1\text{ mA}$	-	150	200	mV
		$I_F = 10\text{ mA}$	-	215	250	mV
		$I_F = 100\text{ mA}$	-	285	340	mV
		$I_F = 500\text{ mA}$	-	380	430	mV
	PMEG4005ET	$I_F = 0.1\text{ mA}$	-	95	130	mV
		$I_F = 1\text{ mA}$	-	155	210	mV
		$I_F = 10\text{ mA}$	-	220	270	mV
		$I_F = 100\text{ mA}$	-	295	350	mV
		$I_F = 500\text{ mA}$	-	420	470	mV
I_R	reverse current					
	PMEG2005ET	$V_R = 10\text{ V}$	-	15	40	μA
		$V_R = 20\text{ V}$	-	40	200	μA
	PMEG3005ET	$V_R = 10\text{ V}$	-	12	30	μA
		$V_R = 30\text{ V}$	-	40	150	μA
	PMEG4005ET	$V_R = 10\text{ V}$	-	7	20	μA
		$V_R = 40\text{ V}$	-	30	100	μA
C_d	diode capacitance		$V_R = 1\text{ V}; f = 1\text{ MHz}$			
	PMEG2005ET		-	66	80	pF
	PMEG3005ET		-	55	70	pF
	PMEG4005ET		-	43	50	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



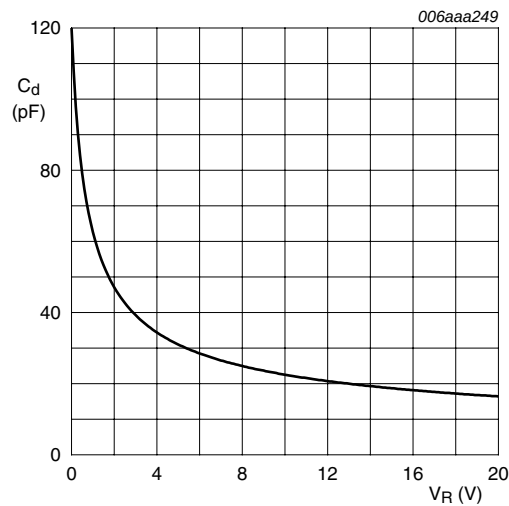
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 1. PMEG2005ET: Forward current as a function of forward voltage; typical values



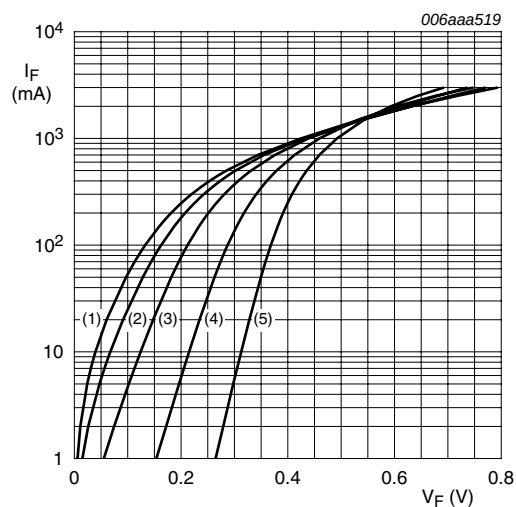
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 2. PMEG2005ET: Reverse current as a function of reverse voltage; typical values



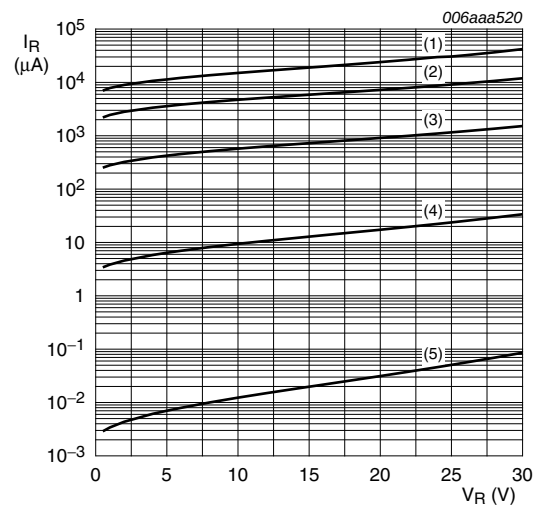
$T_{amb} = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$

Fig 3. PMEG2005ET: Diode capacitance as a function of reverse voltage; typical values



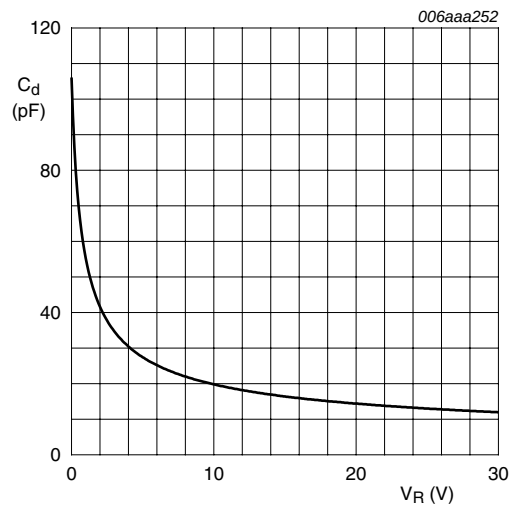
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 4. PMEG3005ET: Forward current as a function of forward voltage; typical values



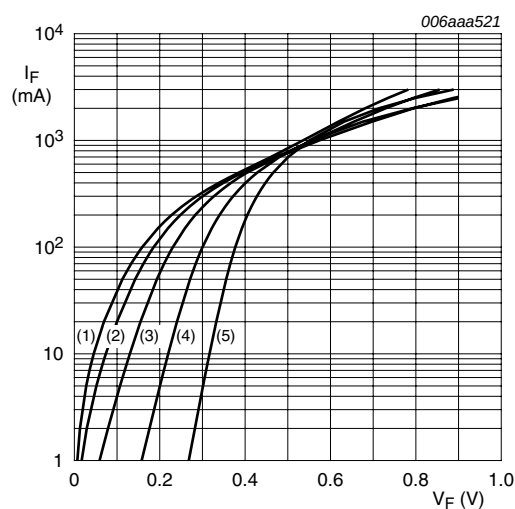
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 5. PMEG3005ET: Reverse current as a function of reverse voltage; typical values



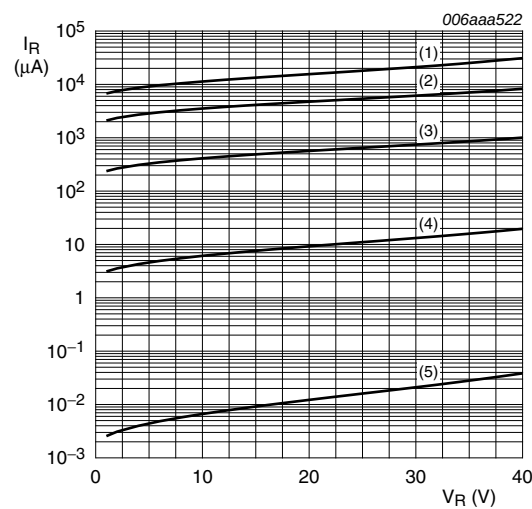
$T_{amb} = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$

Fig 6. PMEG3005ET: Diode capacitance as a function of reverse voltage; typical values



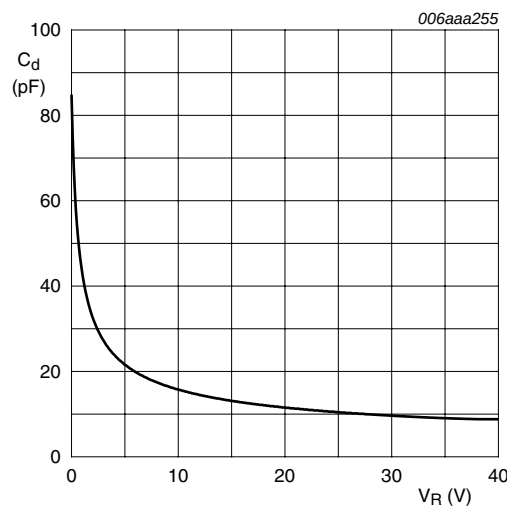
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 7. PMEG4005ET: Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 125\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 85\text{ }^{\circ}\text{C}$
- (4) $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (5) $T_{amb} = -40\text{ }^{\circ}\text{C}$

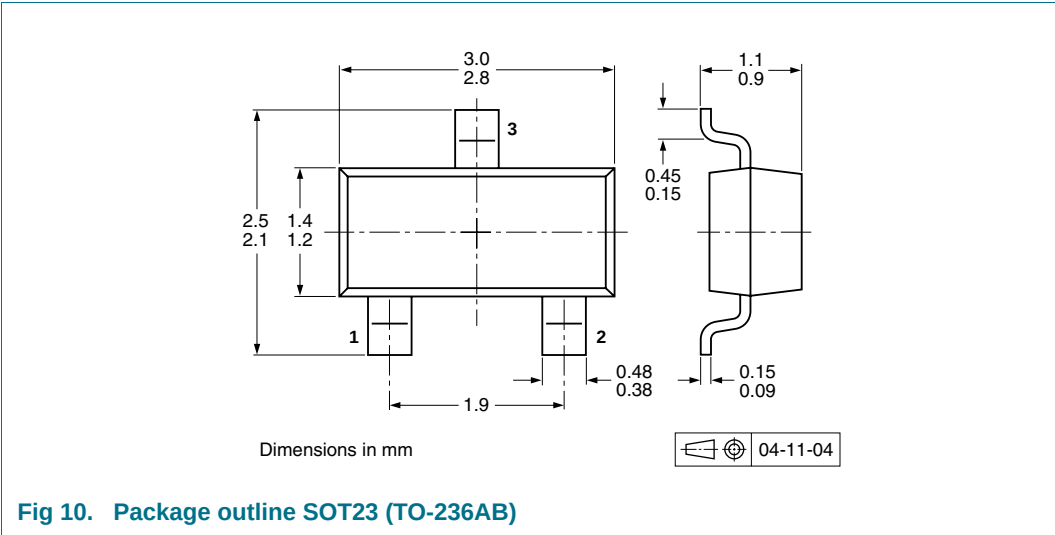
Fig 8. PMEG4005ET: Reverse current as a function of reverse voltage; typical values



$T_{amb} = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$

Fig 9. PMEG4005ET: Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

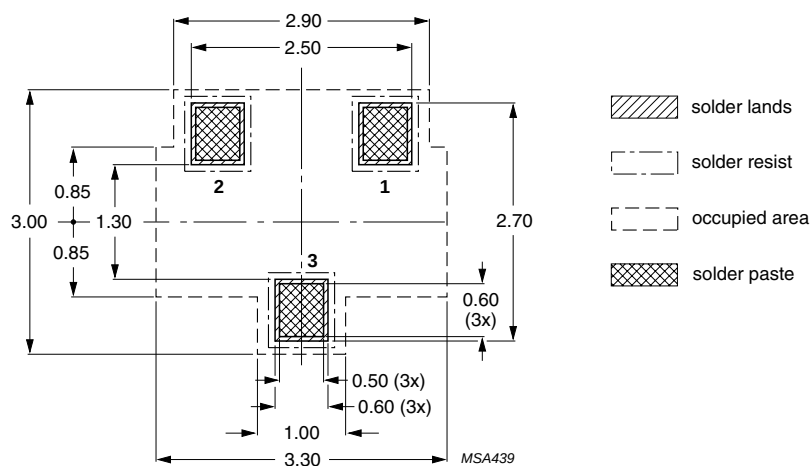
Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG2005ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PMEG3005ET				
PMEG4005ET				

[1] For further information and the availability of packing methods, see [Section 13](#).

10. Soldering



Reflow soldering is the only recommended soldering method.

Dimensions in mm

Fig 11. Reflow soldering footprint SOT23 (TO-236AB)

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEGXX05ET_SER_2	20100113	Product data sheet	-	PMEGXX05ET_SER_1
Modifications:	- This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 11 "Reflow soldering footprint SOT23 (TO-236AB)"; updated			
PMEGXX05ET_SER_1	20050715	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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